Maximum Ratings:
Sub-Component Device: Pre-Biased PNP Transistor (Q1)

@T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{in}	+5 to -6	V
Output Current	I_C	-200	mA

Sub-Component Device: N-MOSFET With Gate Pull-Down Resistor (Q2)

@T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Drain Gate Voltage (R_{GS} ≤1M Ohm)		V_{DGR}	60	V
Gate-Source Voltage	Continuous	V_{GSS}	+/-20	V
	Pulsed (tp<50 uS)		+/-40	
Drain Current (Page 1: Note 3)	Continuous (V_{gs} = 10V)	I_D	115	mA
	Pulsed (tp <10 uS, Duty Cycle <1%)		800	
Continuous Source Current		I_S	115	mA

Electrical Characteristics: Pre-Biased PNP Transistor (Q1) @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Cut Off Current	I_{CBO}	—	—	-100	nA	V_{CB} = -50V, I_E = 0
Collector-Emitter Cut Off Current	I_{CEO}	—	—	-500	nA	V_{CE} = -50V, I_B = 0
Emitter-Base Cut Off Current	I_{EBO}	—	-0.5	-1	mA	V_{EB} = -5V, I_C = 0
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50	—	—	V	I_C = -10 uA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-50	—	—	V	I_C = -2 mA, I_B = 0
Input Off Voltage	$V_{I(OFF)}$	—	-0.55	-0.3	V	V_{CE} = -5V, I_C = -100uA
Output Voltage	V_{OH}	-4.9	—	—	V	V_{CC} = -5V, V_B = -0.05V, R_L = 1K
Ouput Current (leakage current same as I_{CEO})	$I_{O(OFF)}$	—	—	-500	nA	V_{CC} = -50V, V_I = 0V
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	-0.15	V	I_C = -10 mA, I_B = -0.5 mA
		—	—	-0.2	V	I_C = -50mA, I_B = -5mA
		—	—	-0.2	V	I_C = -20mA, I_B = -1mA
		—	—	-0.25	V	I_C = -100mA, I_B= -10mA
		—	—	-0.25	V	I_C = -200mA, I_B= -10mA
		—	—	-0.3	V	I_C = -200mA, I_B = -20mA
Equivalent On-Resistance*	$R_{CE(SAT)}$	—	—	1.5	Ω	I_C = -200mA, I_B = -10mA
DC Current Gain	h_{FE}	60	150	—	—	V_{CE} = -5V, I_C = -20 mA
		60	215	—	—	V_{CE} = -5V, I_C = -50 mA
		60	245	—	—	V_{CE} = -5V, I_C = -100 mA
		60	250	—	—	V_{CE} = -5V, I_C = -200 mA
Input On Voltage	$V_{I(ON)}$	-2.45	-0.7	—	V	V_O = -0.3V, I_C = -2 mA
Output Voltage (equivalent to $V_{CE(SAT)}$ or $V_{O(ON)}$)	V_{OL}	—	-0.065	-0.15	V	V_{CC} = -5V, V_B = -2.5V, I_o/I_I = -50mA /-2.5mA
Input Current	I_i	—	-9	-28	mA	V_I = -5V
Base-Emitter Turn-on Voltage	$V_{BE(ON)}$	—	-1.13	-1.3	V	V_{CE} = -5V, I_C = 200mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-3.2	-3.6	V	I_C = -50mA, I_B = -5mA
		—	-4.6	-5.5		I_C = -80mA, I_B = -8mA
Input Resistor (Base), +/- 30%	R2	—	0.47	—	KΩ	—
Pull-up Resistor (Base to Vcc supply), +/- 30%	R1	—	10	—	KΩ	—
Resistor Ratio (Input Resistor/Pull-up resistor) +/- 20%	R1/R2	—	21	—	—	—
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency (Gain Bandwidth Product)	f_T	—	200	—	MHz	V_{CE} = -10V, I_E = -5mA, f = 100MHz
Collector Capacitance, (C_{cbo}-Output Capacitance)	C_C	—	20	—	pF	V_{CB} = -10V, I_E = 0A, f = 1MHz

* Pulse Test: Pulse width, tp<300 μS, Duty Cycle, d<=0.02

Electrical Characteristics: N-MOSFET with Gate Pull-Down Resistor (Q2)

@T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage, BV_{DSS}	$V_{(BR)DSS}$	60	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current (Drain Leakage Current)	I_{DSS}	—	—	1	μA	V_{GS} =0V, V_{DS} = 60V
Gate-Body Leakage Current, Forward	I_{GSSF}	—	—	0.95	mA	V_{GS} = 20V, V_{DS} = 0V
Gate-Body Leakage Current, Reverse	I_{GSSR}	—	—	-0.95	mA	V_{GS} = -20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Source Threshold Voltage (Control Supply Voltage)	$V_{GS(th)}$	1	1.9	2.2	V	V_{DS} = V_{GS}, I_D = 0.25mA
Static Drain-Source On-State Voltage	$V_{DS(on)}$	—	0.10	1.5	V	V_{GS} = 5V, I_D = 50mA
		—	0.15	3.75		V_{GS} = 10V, I_D = 115mA
On-State Drain Current	$I_{D(on)}$	500	—	—	mA	V_{GS} = 10V, V_{DS} ≥2x$V_{DS(ON)}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	1.6	3	Ω	V_{GS} = 5V, ID = 50mA
		—	1.4	2		V_{GS} = 10V, ID = 500mA
Forward Transconductance	g_{FS}	80	240	—	mS	V_{DS} ≥2x$V_{DS(ON)}$, I_D = 115 mA
		80	350	—		V_{DS} ≥2x$V_{DS(ON)}$, I_D = 200 mA
Gate Pull-Down Resistor, +/- 30%	R3	—	37	—	KΩ	—
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	V_{DS} = -25V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(on)}$	—	—	20	ns	V_{DD} = 30V, V_{GS} =10V, I_D = 200mA, R_G = 25 Ohm, R_L = 150 Ohm
Turn-Off Delay Time	$t_{D(off)}$	—	—	40	ns	
SOURCE-DRAIN (BODY) DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward On-Voltage	V_{SD}	—	0.90	1.5	V	V_{GS} = 0V, I_S = 115 mA
Maximum Continuous Drain-Source Diode Forward Current (Reverse Drain Current)	I_S	—	—	115	mA	—
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}	—	—	800	mA	—

Notes: 4. Short duration pulse test used to minimize self-heating effect.

Typical Characteristics

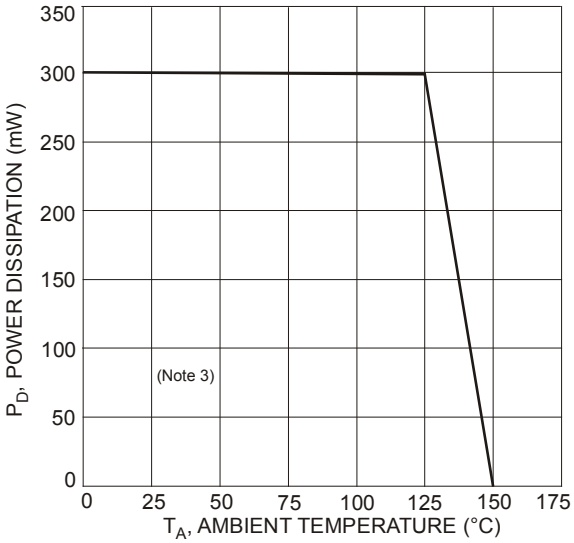


Fig. 3 Max Power Dissipation vs. Ambient Temperature (Total Device)

Typical Pre-Biased PNP Transistor (Q1) Characteristics

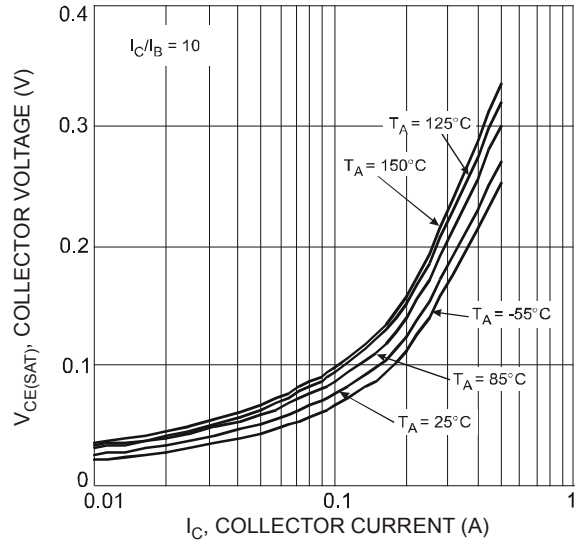


Fig. 4 $V_{CE(SAT)}$ vs. I_C

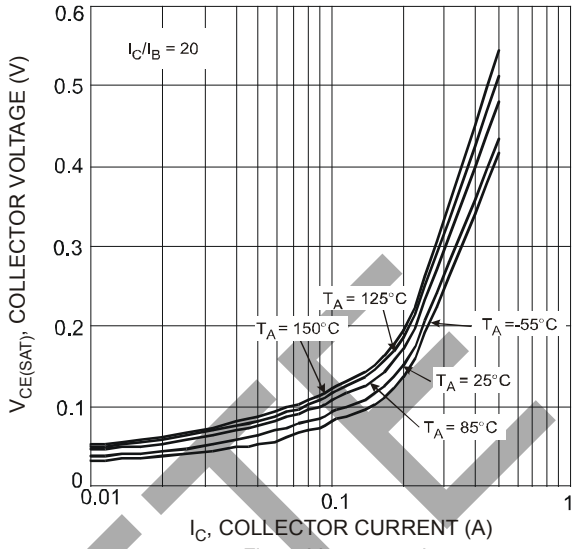


Fig. 5 $V_{CE(SAT)}$ vs. I_C

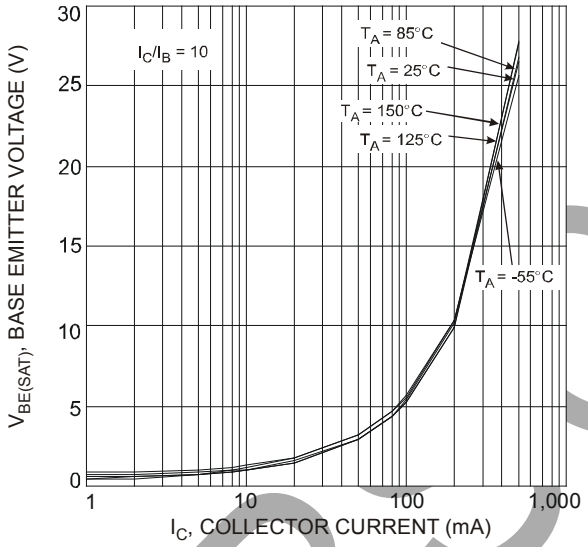


Fig. 6 $V_{BE(SAT)}$ vs. I_C

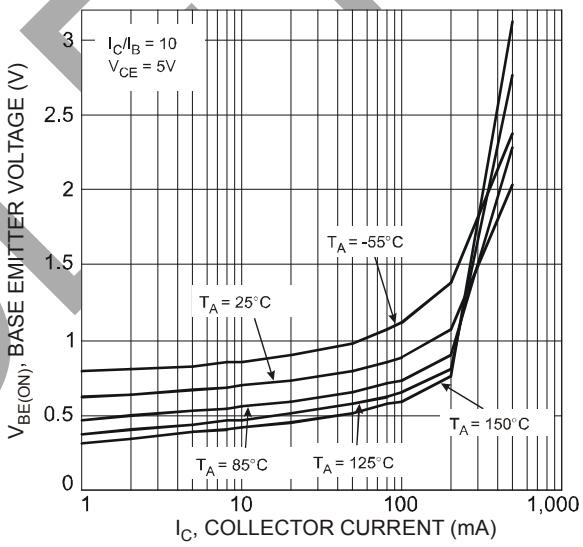


Fig. 7 $V_{BE(ON)}$ vs. I_C

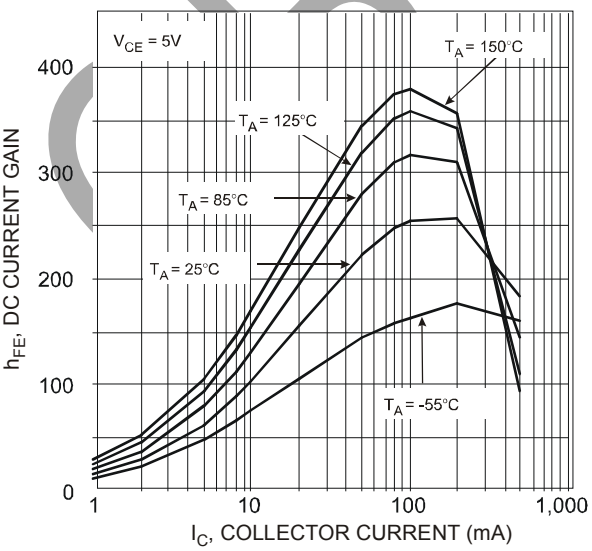


Fig. 8 h_{FE} vs. I_C

Typical N-Channel MOSFET (Q2) Characteristics

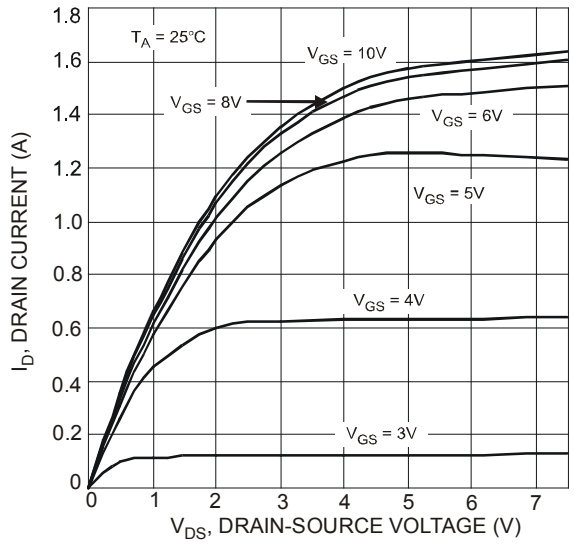


Fig. 9 Output Characteristics

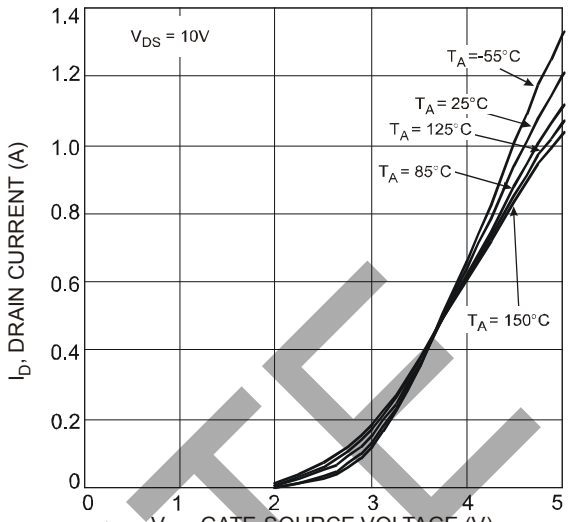


Fig. 10 Transfer Characteristics

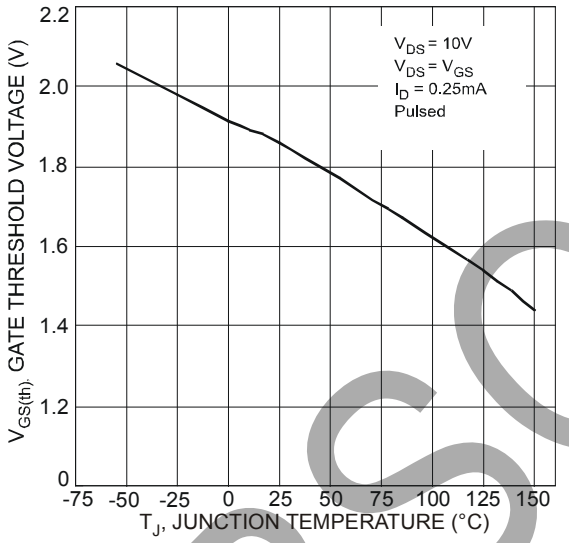


Fig. 11 Gate Threshold Voltage vs. Junction Temperature

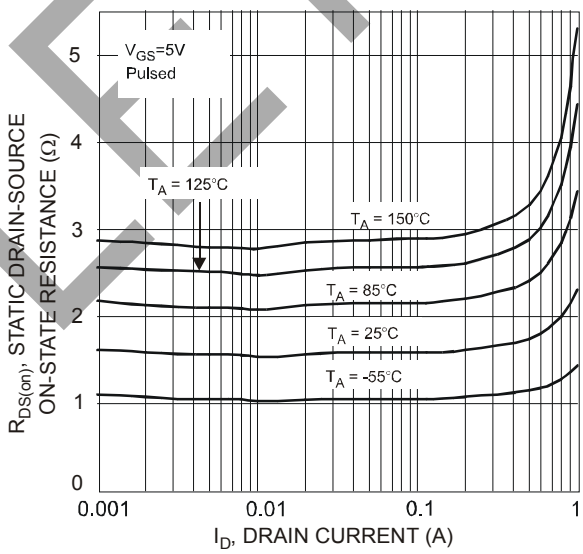


Fig. 12 Static Drain-Source On-Resistance vs. Drain Current

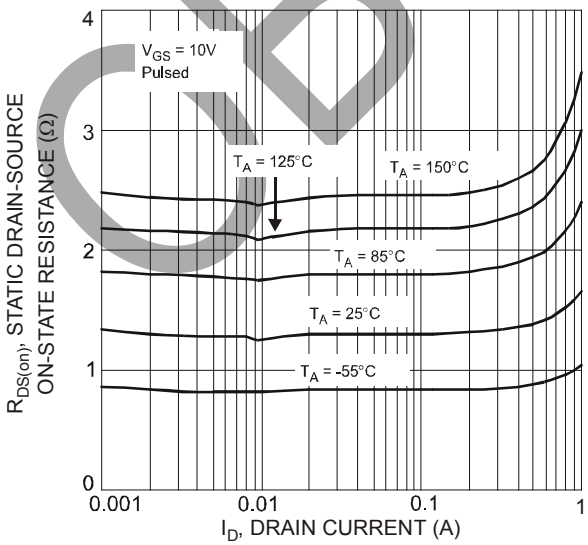


Fig. 13 Static Drain-Source On-Resistance vs. Drain Current

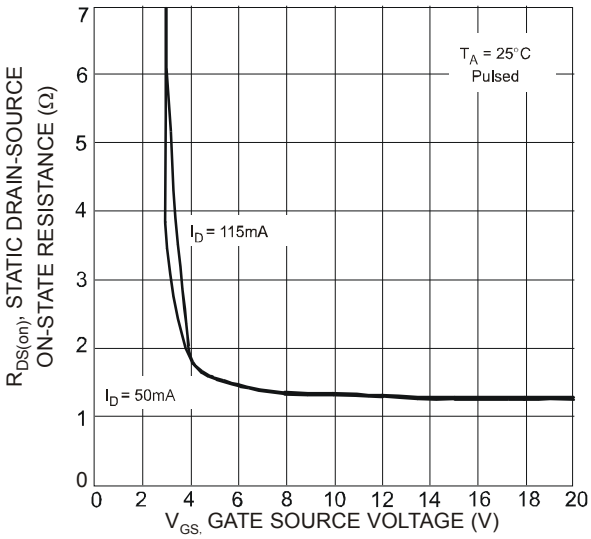


Fig. 14 Static Drain-Source On-Resistance vs. Gate-Source Voltage

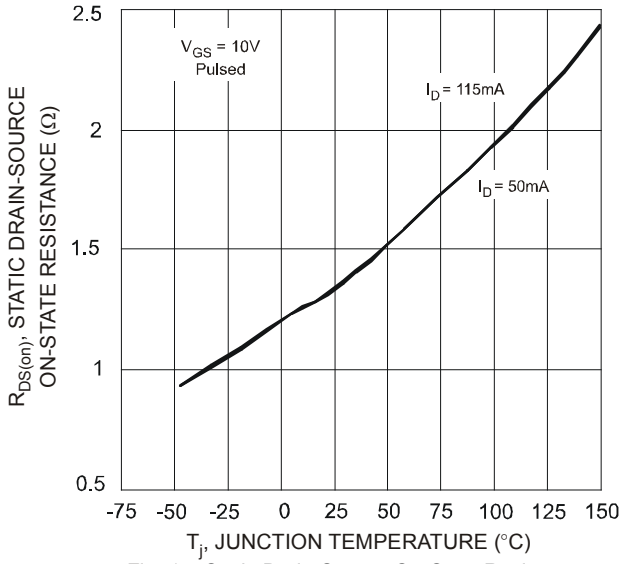


Fig. 15 Static Drain-Source On-State Resistance vs. Junction Temperature

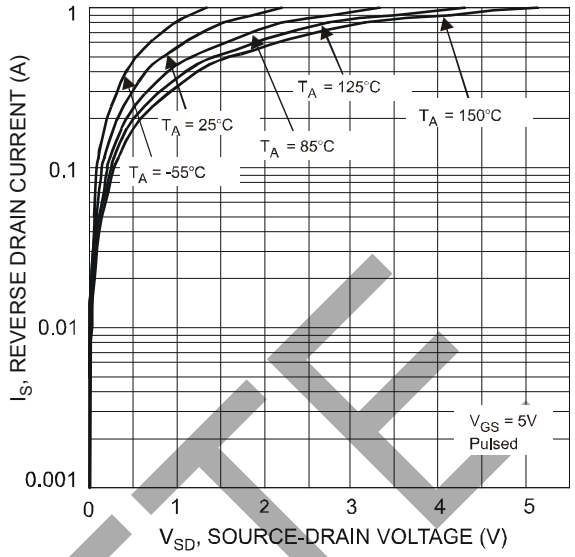


Fig. 16 Reverse Drain Current vs. Source-Drain Voltage

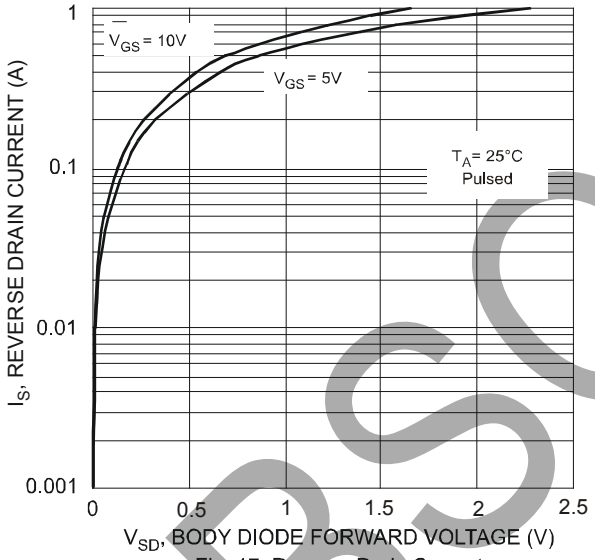


Fig. 17 Reverse Drain Current vs. Body Diode Forward Voltage

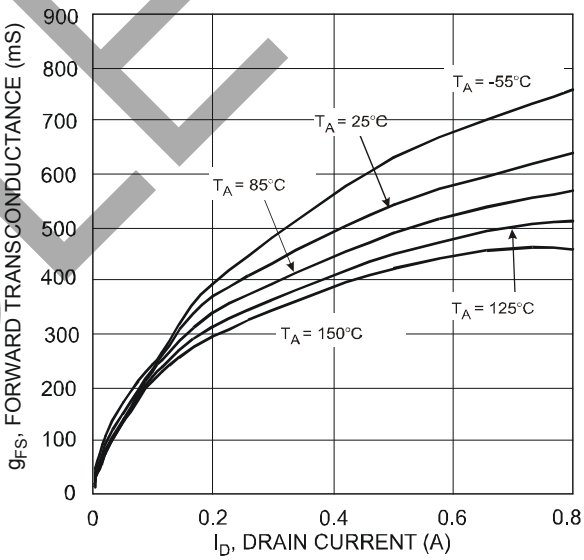


Fig. 18 Forward Transfer Conductance vs. Drain Current ($V_{DS} > I_D R_{DS(ON)}$)

Application Details

PNP Transistor (DDTB142JU) and N-MOSFET (DSNM6047) with gate pull-down resistor integrated as one in LMN200B02 can be used as a discrete entity for general purpose applications or as an integrated circuit to function as a Load Switch. When it is used as the latter as shown in Fig 19, various input voltage sources can be used as long as it does not exceed the maximum ratings of the device. These devices are designed to deliver continuous output load current up to a maximum of 200 mA. The MOSFET Switch draws no current, hence loading of control circuit is prevented. Care must be taken for higher levels of dissipation while designing for higher load conditions. These devices provide high power and also consume less space. The product mainly helps in optimizing power usage, thereby conserving battery life in a controlled load system like portable battery powered applications. (Please see Fig. 20 for one example of a typical application circuit used in conjunction with voltage regulator as a part of a power management system)

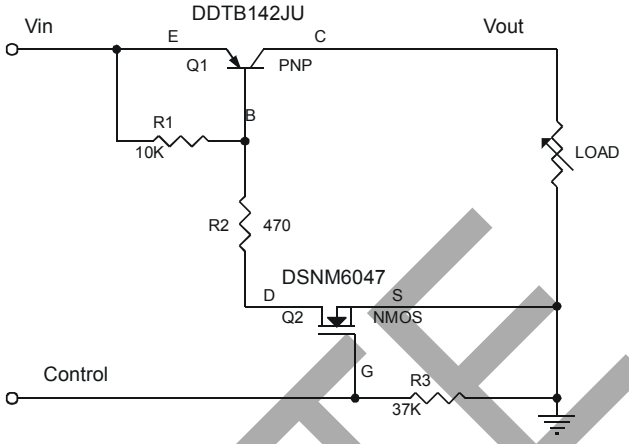


Fig. 19 Circuit Diagram

Typical Application Circuit

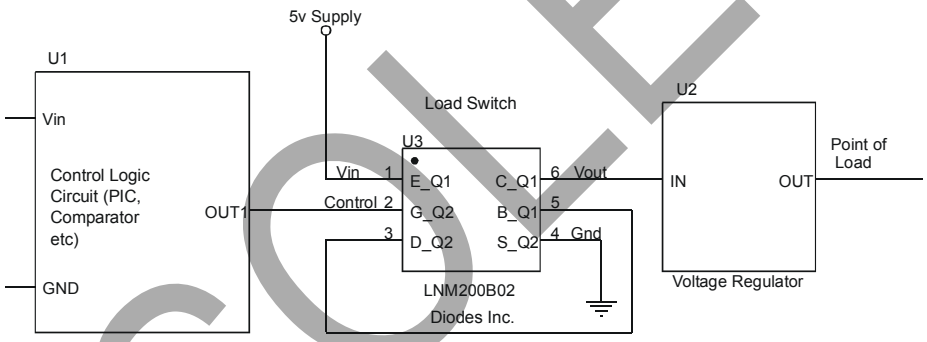


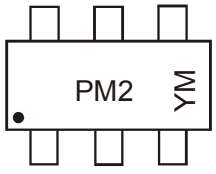
Fig. 20

Ordering Information (Note 5)

Device	Packaging	Shipping
LMN200B02-7	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



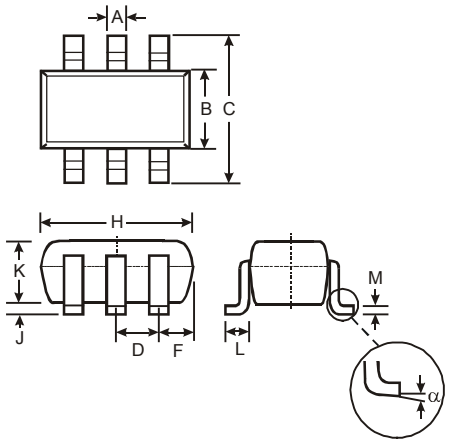
PM2 = Product Type Marking Code,
YM = Date Code Marking
Y = Year (ex: T = 2006)
M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	T	U	V	W	X	Y	Z	A	B	C

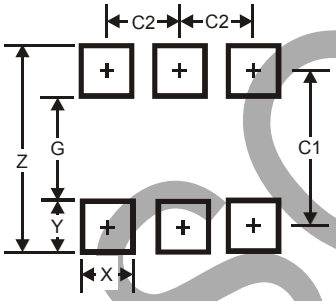
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Mechanical Details



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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